Product Overview

MBRB8H100T4G: Schottky Barrier Rectifier, 100 V, 8.0 A

For complete documentation, see the data sheet

Product Description

The Schottky Rectifier employs the Schottky Barrier principle in a large metal-to-silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for use as rectifiers in low voltage, high frequency inverters, free wheeling diodes and polarity protection diodes.

Features

- Guarding for Stress Protection
- Low Forward Voltage
- 175C Operating Junction Temperature
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Short Heat Sink Tab Manufactured - Not Sheared!
- Case: Molded Expoxy
- Lead and Mounting Surface Temperature for Soldering Purposes: 260C Max. for 10 Seconds
- Epoxy Meets UL94, VO at 1/8
- These are Pb-Free Packages
- NBRB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

Applications

- Switching Power Supplies, Power Inverters

Part Electrical Specifications

Product	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (uA)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_{rr} Max (ns)	C_j Max (pF)	Package Type
MBRB8H100T4G	Pb-free Halide free	Active	Single	100	0.71	4.5	8	250	-	-	D^2PAK-3
NBRB8H100T4G	AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	100	0.71	4.5	8	250	-	-	D^2PAK-3

For more information please contact your local sales support at www.onsemi.com

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